

800V N-CHANNEL MOSFET

GENERAL DESCRIPTION

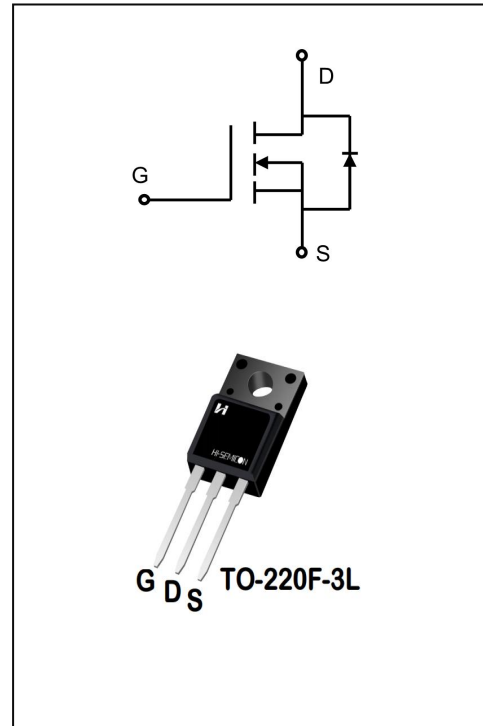
The Power MOSFET is fabricated using advanced super junction technology. The resulting device has extremely low on resistance, making it especially suitable for applications which require superior power density and outstanding efficiency.

Features

- ◆ $V_{DS, min}@T_j(max)=850V$
- ◆ $I_D=6A$
- ◆ $R_{DS(ON)}$
 TYP: $750m\Omega@V_{GS}=10V \quad I_D=3.0A$
 MAX: $950m\Omega$

Applications

- ◆ Power factor correction (PFC)
- ◆ Switched mode power supplies (SMPS)
- ◆ Uninterruptible power supply (UPS)
- ◆ LED lighting power



ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SCF80R950C	TO-220F-3L	SCF80R950C	Pb Free	Tube

ABSOLUTE MAXIMUM RATINGS (T_J=25°C unless otherwise noted)

Characteristics		Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	800	V
Gate-Source Voltage		V _{GS}	±30	V
Drain Current	T _C = 25°C	I _D	6	A
	T _C = 100°C		4.0	
Drain Current Pulsed(Note 1)		I _{DM}	24	A
Power Dissipation(T _C =25°C) -Derate above 25°C		P _D	33	W
			0.28	W/°C
Single Pulsed Avalanche Energy (Note 2)		E _{AS}	247	mJ
Operation Junction Temperature Range		T _J	-55~+150	°C
Storage Temperature Range		T _{stg}	-55~+150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		TL	300	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	MAX	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	3.6	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain -Source Breakdown Voltage	B _{VDS}	V _{GS} =0V, I _D =250μA	800	910	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =800V, V _{GS} =0V	--	--	100	nA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =30V, V _{DS} =0V	--	--	100	nA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =-30V, V _{DS} =0V	--	--	-100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	2	2.7	4.0	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =1A	--	712	940	mΩ
		V _{GS} =10V, I _D =3A	--	750	950	mΩ
Forward Transconductance	g _{FS}	V _{DS} =25V, I _D =6A (Note 3)	--	5.1	--	S
Dynamic Characteristics						
Gate Rresistance	R _g	V _{GS} =0V; f=1.0MHZ	1	4.2	10	Ω
Input Capacitance	C _{iss}	V _{DS} =100V V _{GS} =0V	--	490	--	pF
Output Capacitance	C _{oss}		--	29.6	--	
Reverse Transfer Capacitance	C _{rss}	f=1.0MHZ	--	2.3	--	pF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =400V; V _{GS} =10V R _G =4.7Ω I _D =6A (Note 3.4)	--	9.6	--	ns
Turn-on Rise Time	t _r		--	25	--	
Turn-off Delay Time	t _{d(off)}		--	45	--	
Turn-off Fall Time	t _f		--	26	--	

Total Gate Charge	Q_g	$V_{DS}=640V, I_D=6A$ $V_{GS}=10V$ (Note 3.4)	--	14.9	--	nC
Gate-Source Charge	Q_{gs}		--	1.6	--	
Gate-Drain Charge	Q_{gd}		--	8.1	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	6	A
Pulsed Source Current	I_{SM}		--	--	24	
Diode Forward Voltage	V_{SD}	$I_S=6A, V_{GS}=0V$	--	0.86	1.4	V
Reverse Recovery Time	T_{rr}	$I=6A, V_{GS}=0V,$ $dI/dt=100A/\mu S$ (Note 3)	--	396	--	ns
Reverse Recovery Charge	Q_{rr}		--	4.5	--	μC

NOTE:

1. Pulse width limited by maximum junction temperature
2. $L=79mH, I_{AS}=2.5A, V_{DD}=80V, V_G=10V, R_G=25\Omega$, starting $T_J=25^\circ C$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
4. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Characteristics

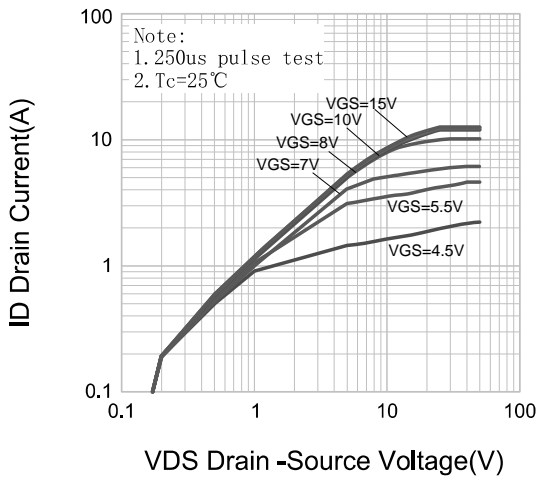


Figure 2. Transfer Characteristics

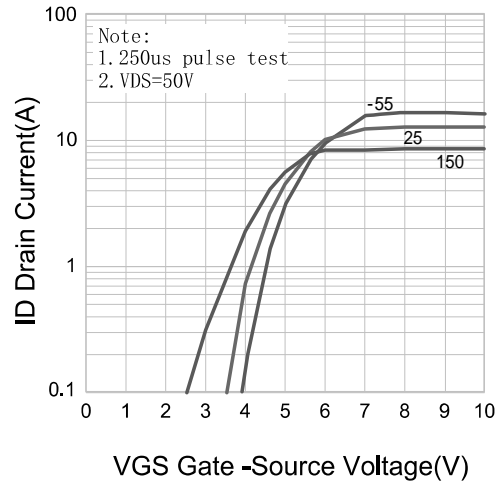


Figure 3. On-Resistance vs Drain Current

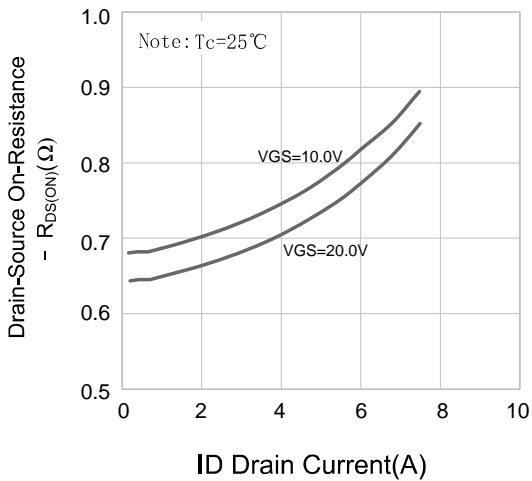


Figure 4. Body Diode Forward Voltage Variation vs Source Current and Temperature

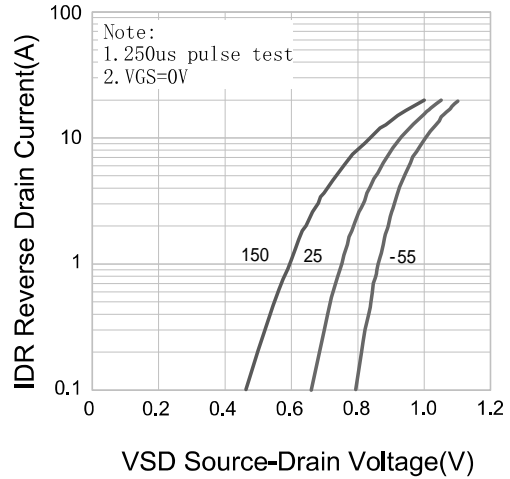


Figure 5. Capacitance Characteristics

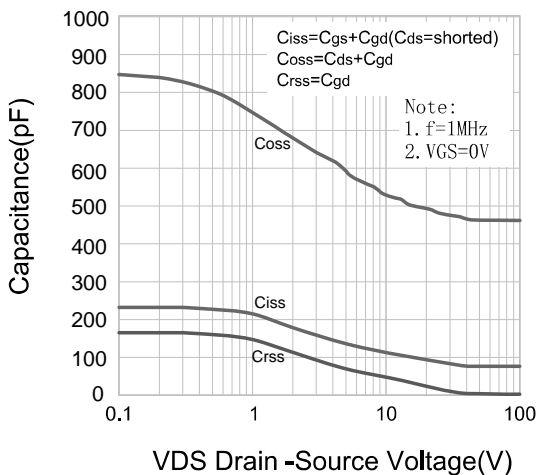
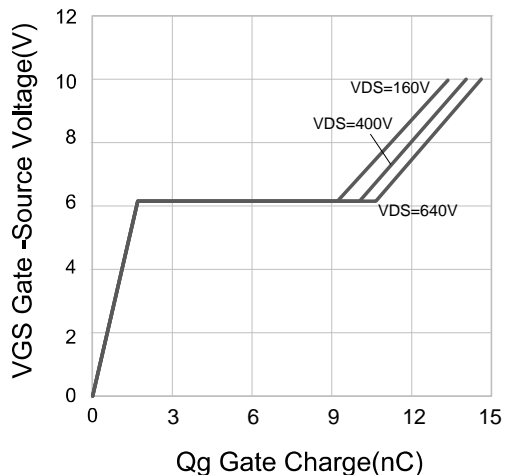


Figure 6. Charge Quantity Characteristics



Typical Performance Characteristics

Figure 7. Breakdown Voltage Variation vs Temperature

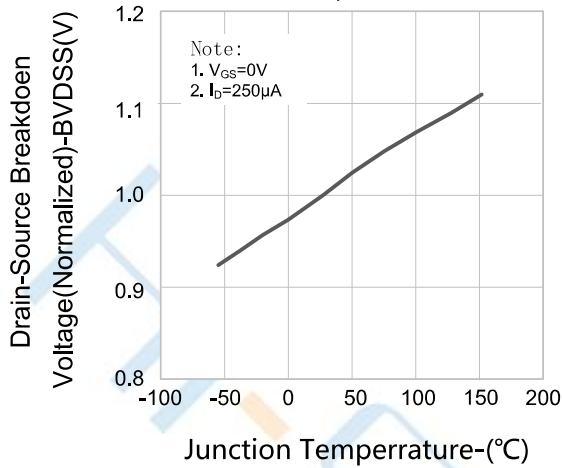


Figure 8. On-resistance Variation vs Temperature

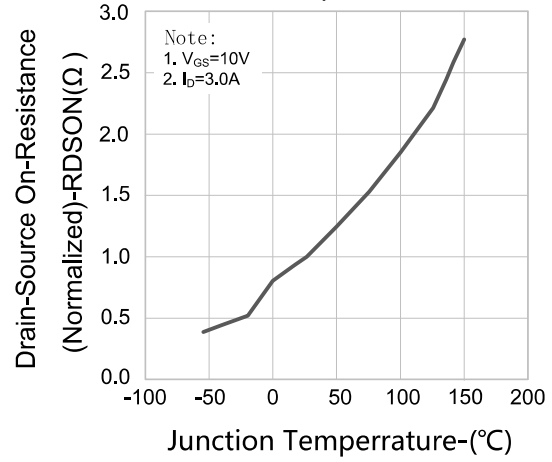
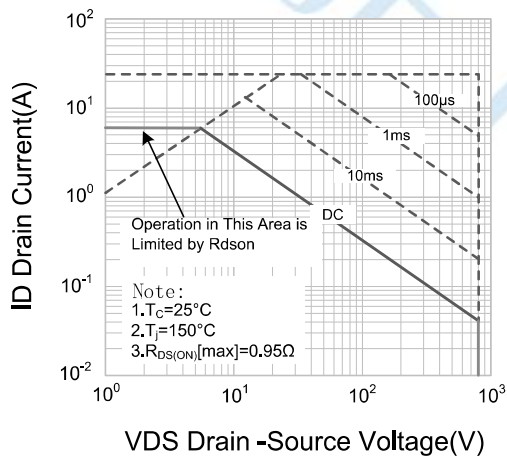
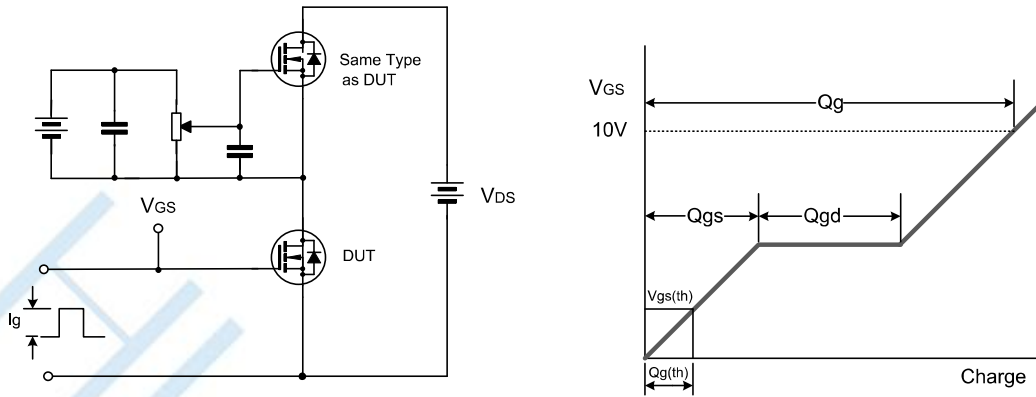


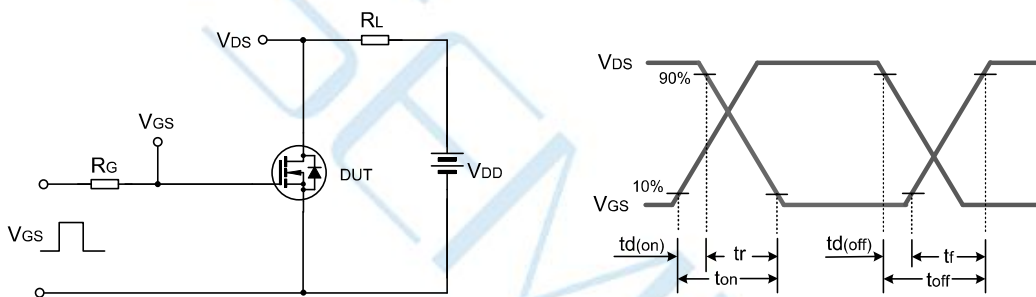
Figure 9. Max Safe Operating Area



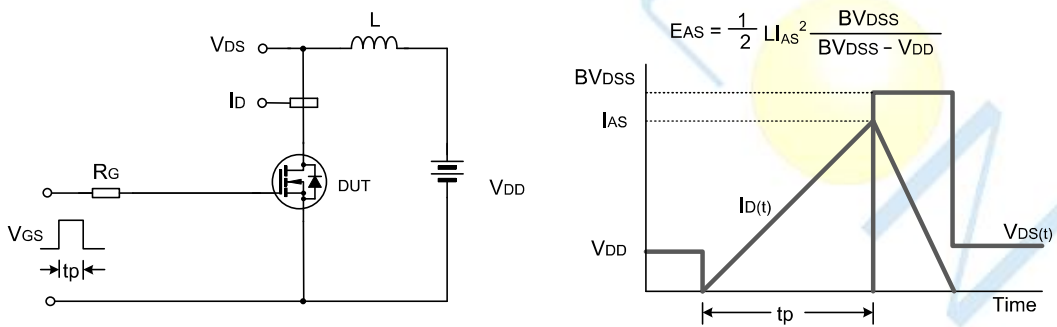
Test Circuit



Gate Charge Test Circuit & Waveform

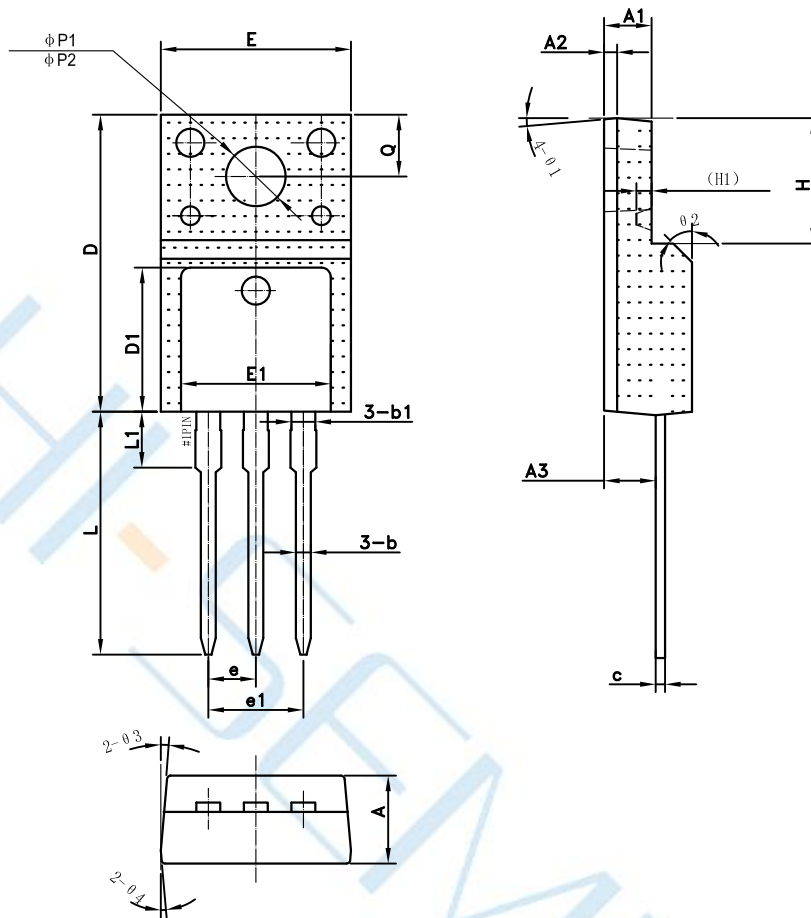


Resistive Switching Test Circuit & Waveform



EAS Test Circuit & Waveform

Package Dimensions of TO-220F-3L



Symbol	Mechanical Dimension/mm		
	Min	Typ	Max
A	4.50	4.70	4.90
A1	2.44	2.54	2.64
A2	0.60	0.70	0.80
A3	2.56	2.76	2.96
b	0.70	0.80	0.95
b1		1.28	
c	0.45	0.50	0.65
D	15.67	15.87	16.07
D1		7.70	
E	9.96	10.16	10.36
E1		8.00	
e		2.54	
e1		5.08	
H	6.50	6.70	6.90
(H1)		(0.81)	
L	12.48	12.98	13.20
L1		2.93	
phi P1	2.98	3.18	3.38
phi P2	3.20	3.40	3.60
Q	3.10	3.30	3.50
theta 1		5°	
theta 2		45°	
theta 3		5°	
theta 4		5°	

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